Galia Pozina

List of Publications by Year
in descending order

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222	4,302	136740	138251
papers	citations	32 h-index	58 g-index

226	226	226	4692
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Design rules for minimizing voltage losses in high-efficiency organic solar cells. Nature Materials, 2018, 17, 703-709.	13.3	701
2	Mechanism for low-temperature photoluminescence in GaNAs/GaAs structures grown by molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 501-503.	1.5	252
3	Synthesis of ZnO nanoparticles by co-precipitation method for solar driven photodegradation of Congo red dye at different pH. Photonics and Nanostructures - Fundamentals and Applications, 2018, 32, 11-18.	1.0	174
4	Evidence for Two Mg Related Acceptors in GaN. Physical Review Letters, 2009, 102, 235501.	2.9	108
5	Growth and excitonic properties of single fractional monolayer CdSe/ZnSe structures. Journal of Applied Physics, 1998, 83, 3168-3171.	1.1	101
6	Mechanism for rapid thermal annealing improvements in undoped GaNxAs1â^'x/GaAs structures grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 2325-2327.	1.5	95
7	Exciton oscillator strength in magnetic-field-induced spin superlattices CdTe/(Cd,Mn)Te. Physical Review B, 1992, 46, 7713-7722.	1.1	94
8	Group III-nitride based hetero and quantum structures. Progress in Quantum Electronics, 2000, 24, 239-290.	3.5	94
9	Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy. Journal of Applied Physics, 1998, 84, 3830-3835.	1.1	83
10	Time-resolved studies of photoluminescence in GaNxP1â^'x alloys: Evidence for indirect-direct band gap crossover. Applied Physics Letters, 2002, 81, 52-54.	1.5	83
11	Perovskite-molecule composite thin films for efficient and stable light-emitting diodes. Nature Communications, 2020, 11, 891.	5.8	83
12	Reducing Thermal Resistance of AlGaN/GaN Electronic Devices Using Novel Nucleation Layers. IEEE Electron Device Letters, 2009, 30, 103-106.	2.2	59
13	Type I band alignment in theGaNxAs1â^'x/GaAsquantum wells. Physical Review B, 2000, 63, .	1.1	57
14	SiC Crystal Growth by HTCVD. Materials Science Forum, 2004, 457-460, 9-14.	0.3	56
15	Origin of multiple peak photoluminescence in InGaN/GaN multiple quantum wells. Journal of Applied Physics, 2000, 88, 2677-2681.	1.1	54
16	Enhancement of spontaneous emission in Tamm plasmon structures. Scientific Reports, 2017, 7, 9014.	1.6	51
17	Bound exciton dynamics in GaN grown by hydride vapor-phase epitaxy. Applied Physics Letters, 1999, 75, 4124-4126.	1.5	49
18	Synthesis of Mg-doped ZnO NPs via a chemical low-temperature method and investigation of the efficient photocatalytic activity for the degradation of dyes under solar light. Solid State Sciences, 2020, 99, 106053.	1.5	46

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19	Phase transformation in Î³- and Î³-Al2O3 coatings on cutting tool inserts. Surface and Coatings Technology, 2009, 203, 1682-1688.	2.2	43
20	Characterisation and Defects in Silicon Carbide. Materials Science Forum, 2002, 389-393, 9-14.	0.3	42
21	Dependence of Resonance Energy Transfer on Exciton Dimensionality. Physical Review Letters, 2011, 107, 236805.	2.9	42
22	Properties of the main Mg-related acceptors in GaN from optical and structural studies. Journal of Applied Physics, 2014, 115, 053507.	1.1	42
23	Emission properties of Ga2O3 nano-flakes: effect of excitation density. Scientific Reports, 2017, 7, 42132.	1.6	42
24	Er/O and Er/F doping during molecular beam epitaxial growth of Si layers for efficient 1.54 Î¼m light emission. Applied Physics Letters, 1997, 70, 3383-3385.	1.5	41
25	Dislocation related droop in InGaN/GaN light emitting diodes investigated via cathodoluminescence. Applied Physics Letters, 2015, 107, .	1.5	39
26	Effect of silicon and oxygen doping on donor bound excitons in bulk GaN. Physical Review B, 2011, 84, .	1.1	38
27	Transient photoluminescence of shallow donor bound excitons in GaN. Physical Review B, 2010, 82, .	1.1	37
28	Hydride vapour phase epitaxy growth and characterization of thick GaN using a vertical HVPE reactor. Journal of Crystal Growth, 2007, 300, 32-36.	0.7	36
29	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. Journal of Applied Physics, 2013, 114, .	1.1	36
30	Giant exciton resonance reflectance in Bragg MQW structures. Superlattices and Microstructures, 1994, 15, 471-473.	1.4	35
31	Radiative recombination in In_{0.15}Ga_{0.85}N/GaN multiple quantum well structures. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	34
32	Luminescence related to high density of Mg-induced stacking faults in homoepitaxially grown GaN. Physical Review B, 2011, 84, .	1.1	34
33	Low-Temperature Kinetics of Localized Excitons in Quantum-Well Structures. Physica Status Solidi (B): Basic Research, 1998, 205, 203-208.	0.7	32
34	Metastable behavior of the UV luminescence in Mg-doped GaN layers grown on quasibulk GaN templates. Applied Physics Letters, 2007, 91, .	1.5	32
35	Size dependent carrier recombination in ZnO nanocrystals. Applied Physics Letters, 2010, 97, .	1.5	32
36	Influence of ZnO seed layer precursor molar ratio on the density of interface defects in low temperature aqueous chemically synthesized ZnO nanorods/GaN light-emitting diodes. Journal of Applied Physics, 2016, 119, .	1.1	30

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37	Mechanism for thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy: Role of nonradiative defects. Applied Physics Letters, 1997, 71, 3676-3678.	1.5	29
38	Optical spectroscopy of GaN grown by metalorganic vapor phase epitaxy using indium surfactant. Applied Physics Letters, 2000, 76, 3388-3390.	1.5	28
39	Optical characterization of III-nitrides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 112-122.	1.7	28
40	Growth of bulk GaN in a vertical hydride vapour phase epitaxy reactor. Superlattices and Microstructures, 2006, 40, 205-213.	1.4	28
41	Indirect optical transition due to surface band bending in ZnO nanotubes. Journal of Applied Physics, 2010, 108, 103513.	1.1	27
42	Optimization of low temperature GaN buffer layers for halide vapor phase epitaxy growth of bulk GaN. Journal of Crystal Growth, 2013, 366, 61-66.	0.7	27
43	Growth of GaN nanotubes by halide vapor phase epitaxy. Nanotechnology, 2011, 22, 085602.	1.3	25
44	Study of planar defect filtering in InP grown on Si by epitaxial lateral overgrowth. Optical Materials Express, 2013, 3, 1960.	1.6	25
45	Parameters of the magnetic polaron state in diluted magnetic semiconductors Cd-Mn-Te with low manganese concentration. Physical Review B, 1996, 54, 5727-5731.	1.1	24
46	Broadening of the excitonic mobility edge in a macroscopically disordered CdSe/ZnSe short-period superlattice. Physical Review B, 1999, 59, R2510-R2513.	1.1	24
47	Influence of polarization fields and depletion fields on photoluminescence of AlGaN/GaN multiple quantum well structures. Physica Status Solidi (B): Basic Research, 2003, 237, 353-364.	0.7	24
48	Resonant Light Delay in GaN with Ballistic and Diffusive Propagation. Physical Review Letters, 2008, 100, 087402.	2.9	24
49	Optical properties of C-doped bulk GaN wafers grown by halide vapor phase epitaxy. Journal of Applied Physics, 2014, 116, .	1.1	24
50	Mechanism for radiative recombination in ZnCdO alloys. Applied Physics Letters, 2007, 90, 261907.	1.5	23
51	Stacking fault related luminescence in GaN nanorods. Nanotechnology, 2015, 26, 355203.	1.3	23
52	MBE growth and properties of bulk BeCdSe alloys and digital (BeSe:CdSe)/ZnSe quantum wells. Journal of Crystal Growth, 2000, 214-215, 109-114.	0.7	22
53	Effects of hydrogen on the optical properties of ZnCdOâˆ•ZnO quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261912.	1.5	22
54	Super-radiant mode in InAsâ€”monolayerâ€“based Bragg structures. Scientific Reports, 2015, 5, 14911.	1.6	22

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55	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. Applied Physics Letters, 2014, 105, .	1.5	21
56	Optical and Transport Properties of CdSe/ZnSe Self-Organized Nanostructures: 1-Dimensional versus 3-Dimensional Quantum Confinement. Japanese Journal of Applied Physics, 1999, 38, 566-569.	0.8	20
57	Atom probe tomography study of Mg-doped GaN layers. Nanotechnology, 2014, 25, 275701.	1.3	20
58	Recombination dynamics and lasing in ZnOâˆ•ZnMgO single quantum well structures. Applied Physics Letters, 2007, 91, 201104.	1.5	19
59	Luminescence of Acceptors in Mg-Doped GaN. Japanese Journal of Applied Physics, 2013, 52, 08JJ03.	0.8	19
60	Characterization of Bulk and Epitaxial SiC Material Using Photoluminescence Spectroscopy. Materials Science Forum, 2002, 389-393, 593-596.	0.3	18
61	Morphological evolution during epitaxial lateral overgrowth of indium phosphide on silicon. Journal of Crystal Growth, 2011, 332, 27-33.	0.7	18
62	Single-emissive-layer all-perovskite white light-emitting diodes employing segregated mixed halide perovskite crystals. Chemical Science, 2020, 11, 11338-11343.	3.7	18
63	Correlation between Si doping and stacking fault related luminescence in homoepitaxial m-plane GaN. Applied Physics Letters, 2013, 103, .	1.5	17
64	Single and double bosonic stimulation of THz emission in polaritonic systems. Scientific Reports, 2014, 4, 5444.	1.6	17
65	Graphene-based plasmonic nanocomposites for highly enhanced solar-driven photocatalytic activities. RSC Advances, 2019, 9, 30585-30598.	1.7	17
66	Development of Î²-Ga2O3 layers growth on sapphire substrates employing modeling of precursors ratio in halide vapor phase epitaxy reactor. Scientific Reports, 2020, 10, 22261.	1.6	17
67	Dynamics of bound excitons versus thickness in freestanding GaN wafers grown by halide vapor phase epitaxy. Applied Physics Letters, 2007, 90, 221904.	1.5	16
68	Effect of the Surface Morphology of Seed and Mask Layers on InP Grown on Si by Epitaxial Lateral Overgrowth. Journal of Electronic Materials, 2012, 41, 2345-2349.	1.0	16
69	Revising of the Purcell effect in periodic metal-dielectric structures: the role of absorption. Scientific Reports, 2019, 9, 9604.	1.6	16
70	Characterization of Red Emission in Nominally Undoped Hydride Vapor Phase Epitaxy GaN. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	15
71	Optical properties of GaNAs/GaAs structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 143-147.	1.7	15
72	Delay and distortion of slow light pulses by excitons in ZnO. Physical Review B, 2011, 84, .	1.1	15

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73	Decoration of ZnO Nanorods with Coral Reefs like NiO Nanostructures by the Hydrothermal Growth Method and Their Luminescence Study. Materials, 2014, 7, 430-440.	1.3	15
74	InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy with mass transport. Applied Physics Letters, 2000, 77, 1638-1640.	1.5	14
75	Time-resolved spectroscopy of strained GaN/AlN/6Hâ€“SiC heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 1062-1064.	1.5	14
76	Si1â^'yCy/Si(001) heterostructures made by sublimation of SiC during silicon molecular beam epitaxy. Applied Physics Letters, 1997, 71, 653-655.	1.5	13
77	Effect of n-type modulation doping on the photoluminescence of GaN/Al0.07Ga0.93N multiple quantum wells. Applied Physics Letters, 2002, 80, 1373-1375.	1.5	13
78	Effect of precursor solutions stirring on deep level defects concentration and spatial distribution in low temperature aqueous chemical synthesis of zinc oxide nanorods. AIP Advances, 2015, 5, .	0.6	13
79	III-nitride tunable cup-cavities supporting quasi whispering gallery modes from ultraviolet to infrared. Scientific Reports, 2016, 5, 17970.	1.6	13
80	Modeling, optimization, and growth of GaN in a vertical halide vapor-phase epitaxy bulk reactor. Journal of Crystal Growth, 2008, 310, 906-910.	0.7	12
81	Deep level study of Mg-doped GaN using deep level transient spectroscopy and minority carrier transient spectroscopy. Physical Review B, 2016, 94, .	1.1	12
82	Synthesis of CuO/ZnO Composite Nanostructures, Their Optical Characterization and Valence Band Offset Determination by X-Ray Photoelectron Spectroscopy. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 348-356.	0.1	12
83	Oscillator strength study of the 2Dâ€“3D exciton transition in CdTe/(Cd,Mn)Te quantum wells and superlattices. Solid State Communications, 1992, 81, 639-642.	0.9	11
84	Effect of annealing on metastable shallow acceptors in Mg-doped GaN layers grown on GaN substrates. Applied Physics Letters, 2008, 92, 151904.	1.5	11
85	Mgâ€related acceptors in GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1850-1852.	0.8	11
86	Optical and structural studies of homoepitaxially grown m-plane GaN. Applied Physics Letters, 2012, 100, .	1.5	11
87	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. Thin Solid Films, 2013, 543, 11-15.	0.8	11
88	Approach to high quality GaN lateral nanowires and planar cavities fabricated by focused ion beam and metal-organic vapor phase epitaxy. Scientific Reports, 2018, 8, 7218.	1.6	11
89	Effect of the electron Coulomb potential on hole confinement in II-VI quantum wells. Physical Review B, 1992, 46, 9788-9791.	1.1	10
90	Photoluminescence in n-doped In0.1Ga0.9N/In0.01Ga0.99N multiple quantum wells. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	10

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91	Suppression of the quantum-confined Stark effect in AlxGa1â^'xN/AlyGa1â^'yN corrugated quantum wells. Journal of Applied Physics, 2013, 114, 124306.	1.1	10
92	Surface potential effect on excitons in AlGaN/GaN quantum well structures. Applied Physics Letters, 2013, 102, 082110.	1.5	10
93	Optical properties of AlGaN/GaN epitaxial layers grown on different face GaN substrates. Materials Letters, 2020, 263, 127229.	1.3	10
94	Efficient UV Luminescence from Organic-Based Tamm Plasmon Structures Emitting in the Strong-Coupling Regime. Journal of Physical Chemistry C, 2020, 124, 21656-21663.	1.5	10
95	Mechanism for Light Emission in GaNAs/GaAs Structures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 125-129.	0.7	9
96	An effective low-temperature solution synthesis of Co-doped [0001]-oriented ZnO nanorods. Journal of Applied Physics, 2017, 121, .	1.1	9
97	Nonlinear behavior of the emission in the periodic structure of InAs monolayers embedded in a GaAs matrix. Physica Status Solidi (B): Basic Research, 2017, 254, 1600402.	0.7	9
98	The 3.466 eV Bound Exciton in GaN. Physica Status Solidi (B): Basic Research, 2001, 228, 489-492.	0.7	8
99	Time resolved photoluminescence study of Si modulation doped GaN/Al0.07Ga0.93N multiple quantum wells. Physica Status Solidi (B): Basic Research, 2004, 241, 1124-1133.	0.7	8
100	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. Journal of Applied Physics, 2016, 119, .	1.1	8
101	Polarization of stacking fault related luminescence in GaN nanorods. AIP Advances, 2017, 7, .	0.6	8
102	Light induced inversion of magnetic hysteresis in CdTe/(Cd,Mn)Te superlattices. Solid-State Electronics, 1994, 37, 1081-1085.	0.8	7
103	Properties of Er-related emission in in situ doped Si epilayers grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1732.	1.6	7
104	Effect of Si doping on structural, photoluminescence and electrical properties of GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 195-197.	1.7	7
105	Optical Properties of an AlInN Interface Layer Spontaneously Formed in Hexagonal InN/Sapphire Heterostructures. Physica Status Solidi (B): Basic Research, 1999, 216, 205-209.	0.7	7
106	Optical and Structural Characterization of Ga(In)N Three-Dimensional Nanostructures Grown by Plasma-Assisted Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 445-450.	0.7	7
107	Luminescence and microstructure of Er/O co-doped Si structures grown by MBE using Er and SiO evaporation. Materials Science in Semiconductor Processing, 2000, 3, 523-528.	1.9	7
108	Growth and characterization of thick GaN layers grown by halide vapour phase epitaxy on lattice-matched AlInN templates. Journal of Crystal Growth, 2009, 311, 292-297.	0.7	7

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109	Defect reduction in heteroepitaxial InP on Si by epitaxial lateral overgrowth. Materials Express, 2014, 4, 41-53.	0.2	7
110	Opposite Sign of Polarization Splitting in Ultrastrongly Coupled Organic Tamm Plasmon Structures. Journal of Physical Chemistry C, 2021, 125, 8376-8381.	1.5	7
111	Optical Studies of Thermally Activated Vertical Hole Transport in ZnCdSe/ZnSSe Superlattice. Acta Physica Polonica A, 1998, 94, 421-426.	0.2	7
112	Proposal for a photoacoustic ultrasonic generator based on Tamm plasmon structures. Optics Express, 2020, 28, 26161.	1.7	7
113	Light emitting SiGe/i-Si/Si:Er:O tunneling diodes prepared by molecular beam epitaxy. Thin Solid Films, 2000, 369, 414-418.	0.8	6
114	Optical Characterization of InGaN/GaN MQW Structures without In Phase Separation. Physica Status Solidi (B): Basic Research, 2001, 228, 157-160.	0.7	6
115	Interface Effects in Type-II CdSe/BeTe Quantum Dots. Physica Status Solidi (B): Basic Research, 2002, 229, 489-492.	0.7	6
116	Metastability of the UV luminescence in Mg-doped GaN layers grown by MOVPE on quasi-bulk GaN templates. Physica B: Condensed Matter, 2007, 401-402, 302-306.	1.3	6
117	Photoluminescence of Mgâ€doped mâ€plane GaN grown by MOCVD on bulk GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1532-1534.	0.8	6
118	Excitonic parameters of GaN studied by time-of-flight spectroscopy. Applied Physics Letters, 2011, 99, 101108.	1.5	6
119	Dynamic properties of excitons in ZnO/AlGaN/GaN hybrid nanostructures. Scientific Reports, 2015, 5, 7889.	1.6	6
120	Seed layer synthesis effect on the concentration of interface defects and emission spectra of ZnO nanorods/pâ€GaN lightâ€emitting diode. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600333.	0.8	6
121	Polyethylene glycol-doped BiZn₂VO₆as a high-efficiency solar-light-activated photocatalyst with substantial durability toward photodegradation of organic contaminations. RSC Advances, 2018, 8, 37480-37491.	1.7	6
122	Resonant reflectivity study of exciton oscillator strength in CdTe/(Cd,Mn)Te quantum wells and superlattices. Journal of Crystal Growth, 1992, 117, 877-880.	0.7	5
123	1.54Î¼m Light emission from Er/O and Er/F doped Si pâ€“iâ€“n diodes grown by molecular beam epitaxy. Journal of Luminescence, 1998, 80, 309-314.	1.5	5
124	<title>Carrier and exciton dynamics in In<formula><inf><roman>0.15</roman></inf></formula>Ga<formula><inf><roman>0.85</roman></inf></formula> NGaN multiple quantum well structures</title>. , 1999, , .		5
125	Time-Resolved Photoluminescence in Strained GaN Layers. Physica Status Solidi A, 2001, 183, 151-155.	1.7	5
126	Optical and structural properties of sulfur-doped ELOG InP on Si. Journal of Applied Physics, 2015, 117, .	1.1	5

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127	IIIâ€nitride microcrystal cavities with quasi whispering gallery modes grown by molecular beam epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 845-852.	0.7	5
128	Near band gap luminescence in hybrid organic-inorganic structures based on sputtered GaN nanorods. Scientific Reports, 2017, 7, 1170.	1.6	5
129	Optical Cavity Based on GaN Planar Nanowires Grown by Selective Area Metalâ€Organic Vapor Phase Epitaxy. Physica Status Solidi (B): Basic Research, 2019, 256, 1800631.	0.7	5
130	Emission Properties of GaN Planar Hexagonal Microcavities. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900894.	0.8	5
131	Quantum analysis of luminescence of an exciton in a meso-cavity. Optics Express, 2021, 29, 20724.	1.7	5
132	Doping of Î²â€Ga₂O₃ Layers by Zn Using Halide Vaporâ€Phase Epitaxy Process. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100486.	0.8	5
133	Optical studies of carrier transport phenomena in CdSe/ZnSe fractional monolayer superlattices. Thin Solid Films, 1998, 336, 377-380.	0.8	4
134	Dynamics of the Bound Excitons in GaN Epilayers Grown by Hydride Vapor Phase Epitaxy. Physica Status Solidi (B): Basic Research, 1999, 216, 45-49.	0.7	4
135	Multiple Peak Spectra from InGaN/GaN Multiple Quantum Wells. Physica Status Solidi A, 2000, 180, 85-89.	1.7	4
136	Excitons as a probe of interface morphology in Cd(Zn)Se/ZnSe heterostructures. Applied Surface Science, 2000, 166, 278-283.	3.1	4
137	Time-resolved optical properties of GaN grown by metalorganic vapor phase epitaxy with indium surfactant. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 82, 137-139.	1.7	4
138	Optical investigation of CdSe/ZnSe quantum nanostructures. Semiconductor Science and Technology, 2002, 17, 173-177.	1.0	4
139	Time-resolved spectroscopy of freestanding GaN layers grown by halide vapour phase epitaxy. Superlattices and Microstructures, 2008, 43, 605-609.	1.4	4
140	High quality InP nanopyramidal frusta on Si. CrystEngComm, 2014, 16, 4624-4632.	1.3	4
141	Weak and strong coupling of photons and excitons in planar meso-cavities. Optics Express, 2020, 28, 12688.	1.7	4
142	Optical characterization of MBE-grown GaNAs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 50, 153-156.	1.7	3
143	Characterization of strained Si/Si[sub 1â^'y]C[sub y] structures prepared by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1621.	1.6	3
144	Characteristics of Si d-Layers Embedded in GaAs. Physica Scripta, 1999, T79, 99.	1.2	3

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145	In-plane and in-depth nonuniformities in defect distribution in GaN and InGaN epilayers. Physica B: Condensed Matter, 2001, 308-310, 102-105.	1.3	3
146	Radiative and Nonradiative Exciton Lifetimes in GaN Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 485-488.	0.7	3
147	Influence of Depletion Fields on Photoluminescence of n-Doped InGaN/GaN Multiple Quantum Well Structures. Physica Status Solidi A, 2002, 192, 21-26.	1.7	3
148	Phase identification in Î³- and Îº-alumina coatings by cathodoluminescence. Scripta Materialia, 2009, 61, 379-382.	2.6	3
149	Properties of GaN layers grown on N-face free-standing GaN substrates. Journal of Crystal Growth, 2015, 413, 81-85.	0.7	3
150	Electronic properties of defects in highâ€fluence electronâ€irradiated bulk GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 521-526.	0.7	3
151	Site-controlled GaN nanocolumns with InGaN insertions grown by MBE. Journal of Physics: Conference Series, 2017, 917, 032032.	0.3	3
152	AlGaN Nanostructures with Extremely High Room-Temperature Internal Quantum Efficiency of Emission Below 300Ânm. Journal of Electronic Materials, 2017, 46, 3888-3893.	1.0	3
153	Different regimes of the Purcell effect in disordered photonic crystals. Journal of Physics Condensed Matter, 2018, 30, 435304.	0.7	3
154	FÃ¶rster Energy Transfer in Arrays of Epitaxial CdSe/ZnSe Quantum Dots Involving Bright and Dark Excitons. Physics of the Solid State, 2018, 60, 1590-1594.	0.2	3
155	Study of Dislocations in Homoepitaxially and Heteroepitaxially Grown AlN Layers. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000465.	0.8	3
156	Control of the surface plasmon dispersion and Purcell effect at the metamaterial-dielectric interface. Scientific Reports, 2020, 10, 20828.	1.6	3
157	Bandgap anomaly and appearance of a monolayer superlattice in InGaAs grown by metal organic chemical vapour deposition. Semiconductor Science and Technology, 1995, 10, 624-626.	1.0	2
158	Incorporation and luminescence properties of Er2O3 and ErF3 doped Si layers grown by molecular beam epitaxy. Thin Solid Films, 1998, 321, 223-227.	0.8	2
159	Optical properties of nanostructures self-organized in CdSe/ZnSe fractional monolayer superlattices. Journal of Crystal Growth, 1999, 201-202, 1231-1234.	0.7	2
160	Dynamics of excitons near the mobility edge in CdSe/ZnSe superlattices. Journal of Crystal Growth, 2000, 214-215, 806-809.	0.7	2
161	Magneto-photoluminescence studies of Cd(Mn)Se/Zn(Mn)Se diluted magnetic nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 362-367.	1.3	2
162	Photoluminescence of InGaN/GaN multiple quantum wells grown by mass transport. Journal of Crystal Growth, 2001, 230, 473-476.	0.7	2

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163	Evidence for type I band alignment in GaNAs/GaAs quantum structures by optical spectroscopies. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1074-1077.	1.3	2
164	DAP emission band in a carbon doped (1â€101)GaN grown on (001)Si substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S772.	0.8	2
165	Photoluminescence of Mg-doped m -plane GaN grown by MOCVD on bulk GaN substrates. Proceedings of SPIE, 2011, , .	0.8	2
166	AlGaN Quantum Well Heterostructures for Mid-Ultraviolet Emitters with Improved Room Temperature Quantum Efficiency. Acta Physica Polonica A, 2014, 126, 1140-1142.	0.2	2
167	Time-resolved photoluminescence properties of hybrids based on inorganic AlGaN/GaN quantum wells and colloidal ZnO nanocrystals. Superlattices and Microstructures, 2015, 87, 38-41.	1.4	2
168	Recombination dynamics in heterostructures with two planar arrays of II-VI quantum dots. Journal of Physics: Conference Series, 2016, 741, 012153.	0.3	2
169	Studies of Er/F Doped p-i-n Si Light Emitting Diodes prepared by Molecular Beam Epitaxy. Physica Scripta, 1999, T79, 155.	1.2	2
170	Photoinduced inversion of magnetic hysteresis in semimagnetic superlattices. Solid State Communications, 1995, 96, 935-941.	0.9	1
171	Optimization of growth conditions for strained Si/Si1â^'yCy structures. Thin Solid Films, 1998, 321, 15-20.	0.8	1
172	Growth of strained structures by MBE. Vacuum, 1998, 49, 185-188.	1.6	1
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